TMUX1119 5V、低リーク電流、2:1 高精度スイッチ

1 特長

- 幅広い電源電圧範囲:1.08V～5.5V
- 小さいリーク電流:3pA
- 低いオン抵抗:1.8Ω
- 少ない電荷注入:–6pC
- -40℃～+125℃の動作温度範囲
- 1.8V ロジック互換
- フェイルセーフ ロジック
- レール ツー レールの動作
- 双方向の信号パス
- ブレイク ビフォー メイクのスイッチング動作
- ESD 保護 (HBM):2000V

2 アプリケーション

- 超音波スキャナ
- メディカル モニタと診断
- 血糖値モニタ
- 光学モジュール
- 光学系トランスポート
- リモート無線ユニット
- データ アクイジション システム
- 半導体試験装置
- ファクトリ オートメーションと産業用制御
- 流量トランスミッタ
- プログラマブル ロジック コントローラ (PLC)
- アナログ入力モジュール
- バッテリ試験装置

3 概要

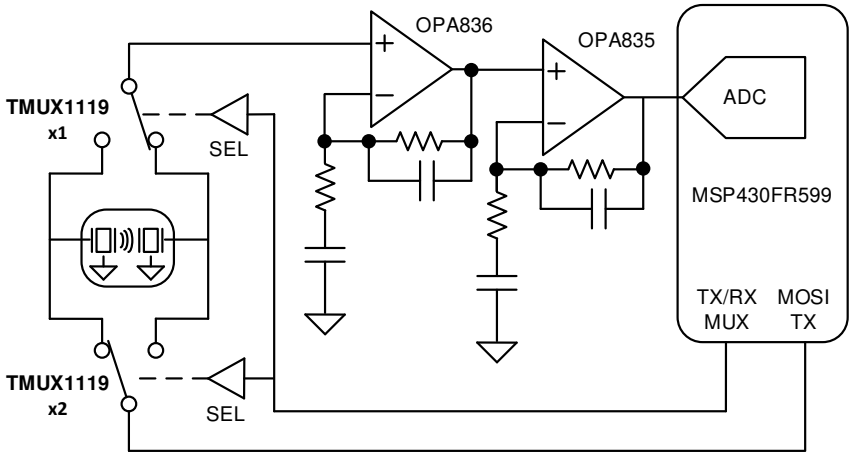
TMUX1119 は、CMOS (相補型金属酸化膜半導体)単極双投(2:1)スイッチです。1.08V～5.5V の広い電源電圧範囲で動作するため、医療機器から産業システムまで、幅広い用途に適しています。このデバイスは、ソース (Sx) およびドレイン (D) ピンで、GND から V_{DD} までの範囲の双方向アナログおよびデジタル信号をサポートします。すべてのロジック入力のスレッショルドは 1.8V ロジック互換で、有効な電源電圧範囲で動作していれば、TTL と CMOS の両方のロジックと互換性を持つことができます。フェイルセーフ ロジック回路により、電源ピンよりも先に制御ピンに電圧が印加されるため、デバイスへの損傷の可能性が避けられます。

TMUX1119 は、高精度スイッチおよびマルチプレクサのデバイス ファミリの製品です。これらのデバイスは、オンおよびオフ時のリーク電流が非常に小さく、電荷注入も少ないため、高精度の測定用途に使用できます。消費電流が 3nA と低く、小さいパッケージ オプションが存在するため、携帯型アプリケーションでも使用できます。

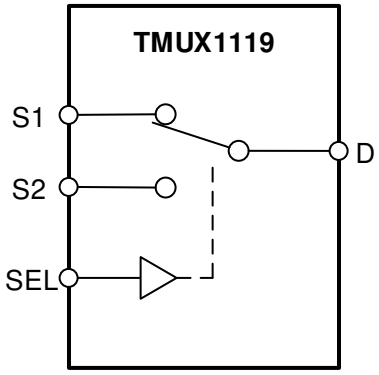
パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ(2)
TMUX1119	DCK (SC70、6)	2mm × 2.1mm
	DBV (SOT-23、6)	2.9mm × 2.8mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。



アプリケーションの例



ブロック図

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4 Pin Configuration and Functions

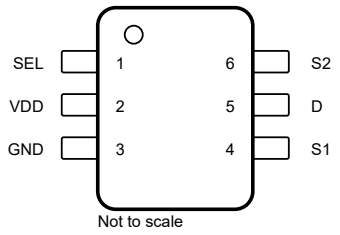


図 4-1. DCK Package, 6-Pin SC70 (Top View)

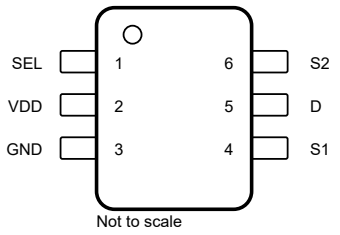


図 4-2. DBV Package, 6-Pin SOT-23 (Top View)

表 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
SEL	1	I	Select pin: controls state of the switch according to 表 7-1. (Logic Low = S1 to D, Logic High = S2 to D)
VDD	2	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1µF to 10µF between V_{DD} and GND.
GND	3	P	Ground (0V) reference
S1	4	I/O	Source pin 1. Can be an input or output.
D	5	I/O	Drain pin. Can be an input or output.
S2	6	I/O	Source pin 2. Can be an input or output.

(1) I = input, O = output, I/O = input and output, P = power

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	–0.5	6	V
V_{SEL} or V_{EN}	Logic control input pin voltage (SEL)	–0.5	6	V
I_{SEL} or I_{EN}	Logic control input pin current (SEL)	–30	30	mA
V_S or V_D	Source or drain voltage (Sx, D)	–0.5	V_{DD}+0.5	V
I_S or $I_{D\ (CONT)}$	Source or drain continuous current (Sx, D)	I_{DC} ± 10 %(3)	I_{DC} ± 10 %(3)	mA
I_S or $I_{D\ (PEAK)}$	Source and drain peak current: (1 ms period maximum, 10% duty cycle maximum) (Sx, D)	Ipeak ± 10 %(3)	Ipeak ± 10 %(3)	mA
T_{stg}	Storage temperature	–65	150	°C
P_{tot}	Total power dissipation(4) (5)		300	mW
T_J	Junction temperature		150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) Refer to Recommended Operating Conditions for I_{DC} and I_{Peak} ratings
(4) For DCK(SC70) package: P_{tot} derates linearly above TA=77°C by 4.11mW/°C
(5) For DGS(SOT-23) package: P_{tot} derates linearly above TA=86°C by 4.71mW/°C

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage		1.08		5.5	V
V_S or V_D	Signal path input/output voltage (source or drain pin) (Sx, D)		0		V_{DD}	V
V_{SEL}	Logic control input pin voltage (SEL)		0		5.5	V
T_A	Ambient temperature		–40		125	°C
I_{DC}	Continuous current through switch	Tj = 25°C		150		
		Tj = 85°C		120		mA
		Tj = 125°C		60		mA
		Tj = 130°C		50		mA
I_{peak}	Peak current through switch(1 ms period maximum, 10% duty cycle maximum)	Tj = 25°C		300		mA
		Tj = 85°C		300		mA
		Tj = 125°C		180		mA
		Tj = 130°C		160		mA

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5.4 Thermal Information

THERMAL METRIC[1]		TMUX1119		UNIT
		DCK (SC70)	DBV (SOT-23)	
		6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	243.1	212.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	206.0	156.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	128.3	96.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	107.8	80.7	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	128.0	96.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics (V_{DD} = 5V ±10 %)

At T_A = 25°C, V_{DD} = 5V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		1.8	4	Ω
			–40°C to +85°C			4.5	Ω
			–40°C to +125°C			4.9	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		0.13		Ω
			–40°C to +85°C			0.4	Ω
			–40°C to +125°C			0.5	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		0.85		Ω
			–40°C to +85°C			1.4	Ω
			–40°C to +125°C			1.6	Ω
$I_{S(OFF)}$	Source off leakage current[1]	V_{DD} = 5V Switch Off V_D = 4.5V / 1.5V V_S = 1.5V / 4.5V Refer to セクション 6.2	25°C	–0.08	±0.005	0.08	nA
			–40°C to +85°C	–0.3		0.3	nA
			–40°C to +125°C	–0.9		0.9	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 5V Switch On V_D = V_S = 2.5V Refer to セクション 6.3	25°C	–0.025	±0.003	0.025	nA
			–40°C to +85°C	–0.3		0.3	nA
			–40°C to +125°C	–0.95		0.95	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 5V Switch On V_D = V_S = 4.5V / 1.5V Refer to セクション 6.3	25°C	–0.1	±0.01	0.1	nA
			–40°C to +85°C	–0.35		0.35	nA
			–40°C to +125°C	–2		2	nA
LOGIC INPUTS (SEL)							
V_{IH}	Input logic high		–40°C to +125°C	1.49		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.87	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF

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5.5 Electrical Characteristics (V_{DD} = 5V ±10 %) (続き)

At T_A = 25°C, V_{DD} = 5V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0V or 5.5V	25°C		0.003		µA
			–40°C to +125°C			1	µA
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_S = 3V R_L = 200Ω, C_L = 15pF Refer to セクション 6.4	25°C		12		ns
			–40°C to +85°C			18	ns
			–40°C to +125°C			19	ns
t_{OPEN} (BBM)	Break before make time	V_S = 3V R_L = 200Ω, C_L = 15pF Refer to セクション 6.5	25°C		8		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_D = 1V R_S = 0Ω, C_L = 1 nF Refer to セクション 6.6	25°C		–6		pC
O_{ISO}	Off Isolation	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.7	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.7	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.8	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.8	25°C		–45		dB
BW	Bandwidth	R_L = 50Ω, C_L = 5pF Refer to セクション 6.9	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1MHz	25°C		6		pF
C_{SON} C_{DON}	On capacitance	f = 1MHz	25°C		20		pF

(1) When V_S is 4.5V, V_D is 1.5V, and vice versa.

5.6 Electrical Characteristics (V_{DD} = 3.3V ±10 %)

At T_A = 25°C, V_{DD} = 3.3V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		3.7	8.8	Ω
			–40°C to +85°C			9.5	Ω
			–40°C to +125°C			9.8	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		0.13		Ω
			–40°C to +85°C			0.4	Ω
			–40°C to +125°C			0.5	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		1.9		Ω
			–40°C to +85°C		2		Ω
			–40°C to +125°C		2.2		Ω

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5.6 Electrical Characteristics (V_{DD} = 3.3V ±10 %) (続き)

At T_A = 25°C, V_{DD} = 3.3V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 3.3V Switch Off V_D = 3V / 1V V_S = 1V / 3V Refer to セクション 6.2	25°C	–0.05	±0.001	0.05	nA
			–40°C to +85°C	–0.1		0.1	nA
			–40°C to +125°C	–0.5		0.5	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 3.3V Switch On V_D = V_S = 3V / 1V Refer to セクション 6.3	25°C	–0.1	±0.005	0.1	nA
			–40°C to +85°C	–0.35		0.35	nA
			–40°C to +125°C	–2		2	nA
LOGIC INPUTS (SEL)							
V_{IH}	Input logic high		–40°C to +125°C	1.35		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.8	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		-40°C to 125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0V or 5.5V	25°C		0.003		µA
			–40°C to +125°C			0.8	µA
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_S = 2V R_L = 200Ω, C_L = 15pF Refer to セクション 6.4	25°C		14		ns
			–40°C to +85°C			20	ns
			–40°C to +125°C			21	ns
t_{OPEN} (BBM)	Break before make time	V_S = 2V R_L = 200Ω, C_L = 15pF Refer to セクション 6.5	25°C		9		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_D = 1V R_S = 0Ω, C_L = 1 nF Refer to セクション 6.6	25°C		–6		pC
O_{ISO}	Off Isolation	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.7	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.7	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.8	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.8	25°C		–45		dB
BW	Bandwidth	R_L = 50Ω, C_L = 5pF Refer to セクション 6.9	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1MHz	25°C		6		pF
C_{SON} C_{DON}	On capacitance	f = 1MHz	25°C		20		pF

(1) When V_S is 3V, V_D is 1V, and vice versa.

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5.7 Electrical Characteristics (V_{DD} = 1.8V ±10 %)

At T_A = 25°C, V_{DD} = 1.8V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		40		Ω
			–40°C to +85°C			80	Ω
			–40°C to +125°C			80	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		0.4		Ω
			–40°C to +85°C			1.5	Ω
			–40°C to +125°C			1.5	Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 1.98V Switch Off V_D = 1.62V / 1V V_S = 1V / 1.62V Refer to セクション 6.2	25°C	–0.05	±0.003	0.05	nA
			–40°C to +85°C	–0.1		0.1	nA
			–40°C to +125°C	–0.5		0.5	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 1.98V Switch On V_D = V_S = 1.62V / 1V Refer to セクション 6.3	25°C	–0.1	±0.005	0.1	nA
			–40°C to +85°C	–0.5		0.5	nA
			–40°C to +125°C	–2		2	nA
LOGIC INPUTS (SEL)							
V_{IH}	Input logic high		–40°C to +125°C	1.07		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.68	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0V or 5.5V	25°C		0.001		µA
			–40°C to +125°C			0.85	µA
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	V_S = 1V R_L = 200Ω, C_L = 15pF Refer to セクション 6.4	25°C		28		ns
			–40°C to +85°C			44	ns
			–40°C to +125°C			44	ns
t_{OPEN} (BBM)	Break before make time	V_S = 1V R_L = 200Ω, C_L = 15pF Refer to セクション 6.5	25°C		16		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_D = 1V R_S = 0Ω, C_L = 1 nF Refer to セクション 6.6	25°C		–3		pC
O_{ISO}	Off Isolation	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.7	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.7	25°C		–45		dB

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5.7 Electrical Characteristics (V_{DD} = 1.8V ±10 %) (続き)

At T_A = 25°C, V_{DD} = 1.8V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
X_{TALK}	Crosstalk	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.8	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.8	25°C		–45		dB
BW	Bandwidth	R_L = 50Ω, C_L = 5pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1MHz	25°C		6		pF
C_{SON} C_{DON}	On capacitance	f = 1MHz	25°C		20		pF

(1) When V_S is 1.62V, V_D is 1V, and vice versa.

5.8 Electrical Characteristics (V_{DD} = 1.2V ±10 %)

At T_A = 25°C, V_{DD} = 1.2V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		70		Ω
			–40°C to +85°C			105	Ω
			–40°C to +125°C			105	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0V to V_{DD} I_{SD} = 10mA Refer to セクション 6.1	25°C		0.4		Ω
			–40°C to +85°C			1.5	Ω
			–40°C to +125°C			1.5	Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 1.32V Switch Off V_D = 1V / 0.8V V_S = 0.8V / 1V Refer to セクション 6.2	25°C	–0.05	±0.003	0.05	nA
			–40°C to +85°C	–0.1		0.1	nA
			–40°C to +125°C	–0.5		0.5	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 1.32V Switch On V_D = V_S = 1V / 0.8V Refer to セクション 6.3	25°C	–0.1	±0.005	0.1	nA
			–40°C to +85°C	–0.5		0.5	nA
			–40°C to +125°C	–2		2	nA
LOGIC INPUTS (SEL)							
V_{IH}	Input logic high		–40°C to +125°C	0.96		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.36	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic inputs = 0V or 5.5V	25°C		0.003		µA
			–40°C to +125°C			0.7	µA
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Transition time between channels	V_S = 1V R_L = 200Ω, C_L = 15pF Refer to セクション 6.4	25°C		55		ns
			–40°C to +85°C			190	ns
			–40°C to +125°C			190	ns

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5.8 Electrical Characteristics (V_{DD} = 1.2V ±10 %) (続き)

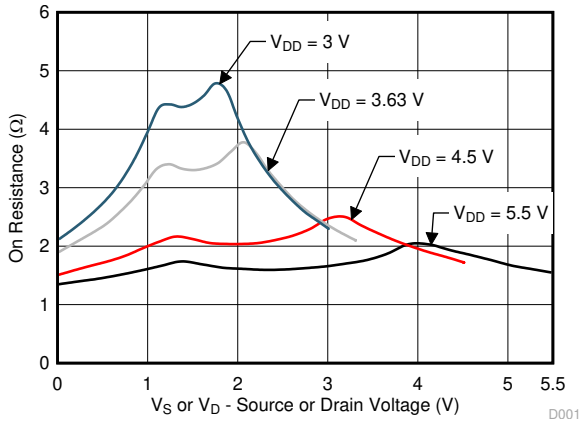
At T_A = 25°C, V_{DD} = 1.2V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
t_{OPEN} (BBM)	Break before make time	V_S = 1V R_L = 200Ω, C_L = 15pF Refer to セクション 6.5	25°C		28		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_D = 1V R_S = 0Ω, C_L = 1 nF Refer to セクション 6.6	25°C		–2		pC
O_{ISO}	Off Isolation	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.7	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.7	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50Ω, C_L = 5pF f = 1MHz Refer to セクション 6.8	25°C		–65		dB
		R_L = 50Ω, C_L = 5pF f = 10MHz Refer to セクション 6.8	25°C		–45		dB
BW	Bandwidth	R_L = 50Ω, C_L = 5pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1MHz	25°C		6		pF
C_{SON} C_{DON}	On capacitance	f = 1MHz	25°C		20		pF

(1) When V_S is 1V, V_D is 0.8V, and vice versa.

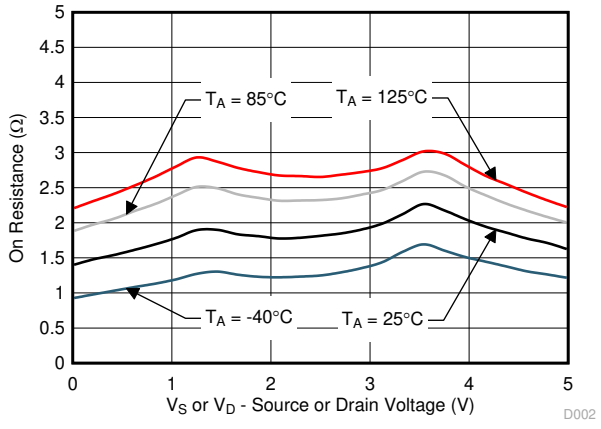
Typical Characteristics

at T_A = 25°C, V_{DD} = 5V (unless otherwise noted)



T_A = 25°C

図 5-1. On-Resistance vs Source or Drain Voltage

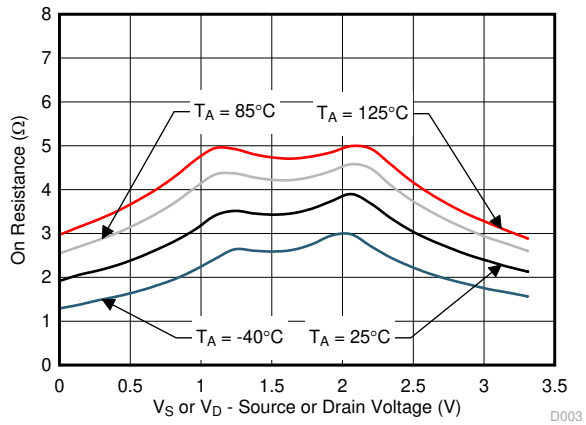


V_{DD} = 5V

図 5-2. On-Resistance vs Temperature

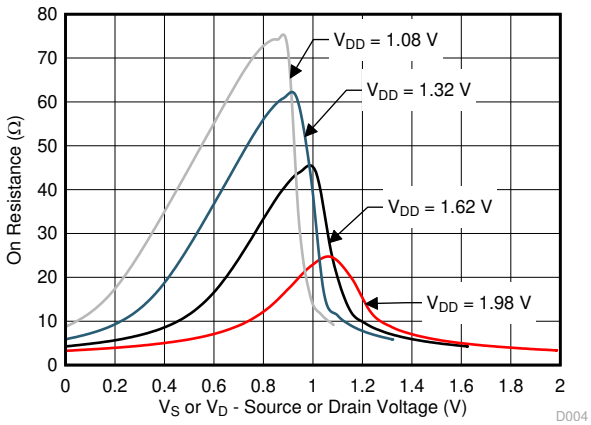
Typical Characteristics

at T_A = 25°C, V_{DD} = 5V (unless otherwise noted)



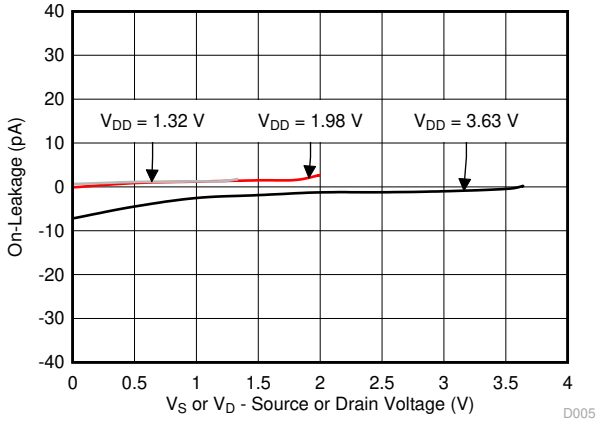
V_{DD} = 3.3V

図 5-3. On-Resistance vs Temperature



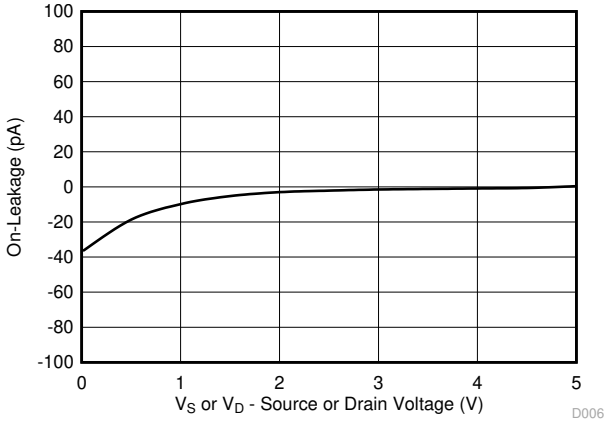
T_A = 25°C

図 5-4. On-Resistance vs Source or Drain Voltage



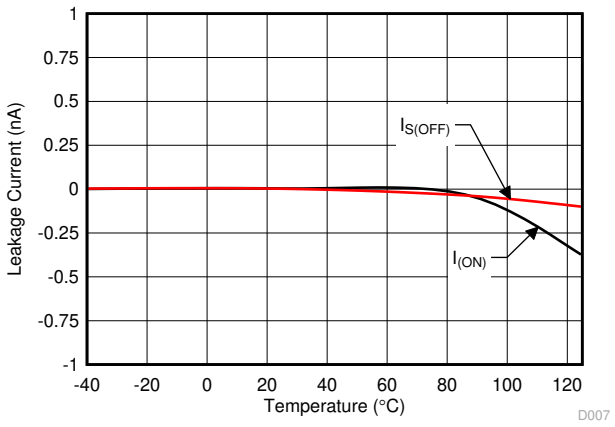
T_A = 25°C

図 5-5. On-Leakage vs Source or Drain Voltage



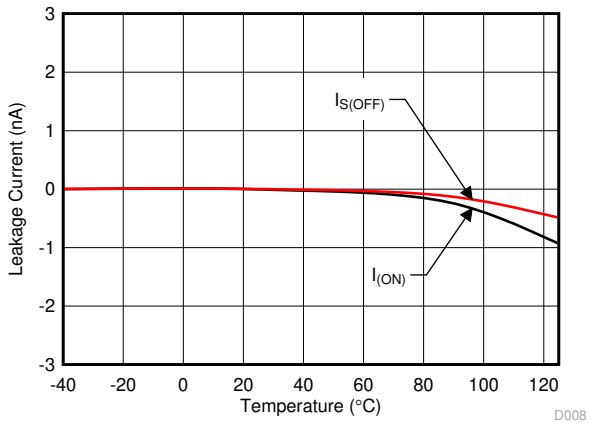
V_{DD} = 5V

図 5-6. On-Leakage vs Source or Drain Voltage



V_{DD} = 3.3V

図 5-7. Leakage Current vs Temperature



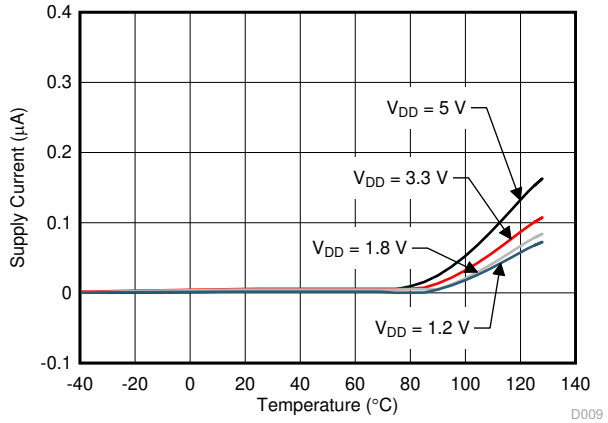
V_{DD} = 5V

図 5-8. Leakage Current vs Temperature

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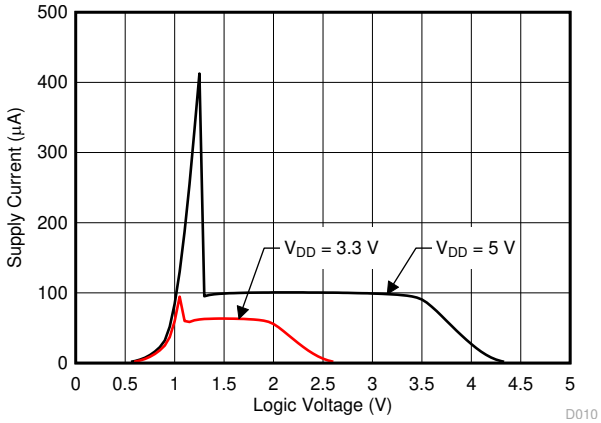
Typical Characteristics

at T_A = 25°C, V_{DD} = 5V (unless otherwise noted)



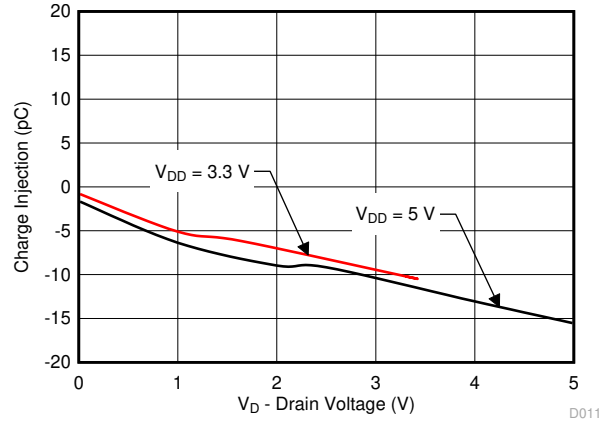
V_{SEL} = 5.5V

図 5-9. Supply Current vs Temperature



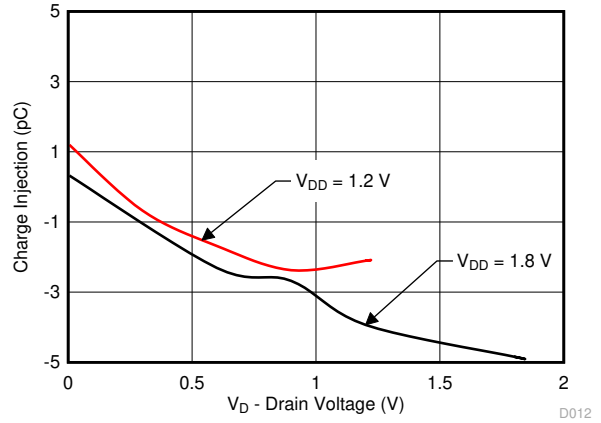
T_A = 25°C

図 5-10. Supply Current vs Logic Voltage



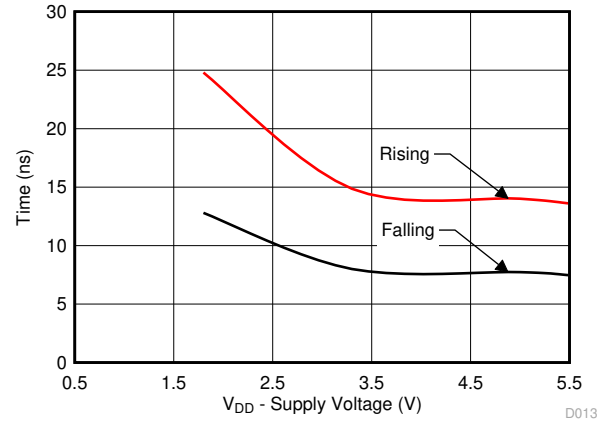
T_A = -40°C to 125°C

図 5-11. Charge Injection vs Drain Voltage



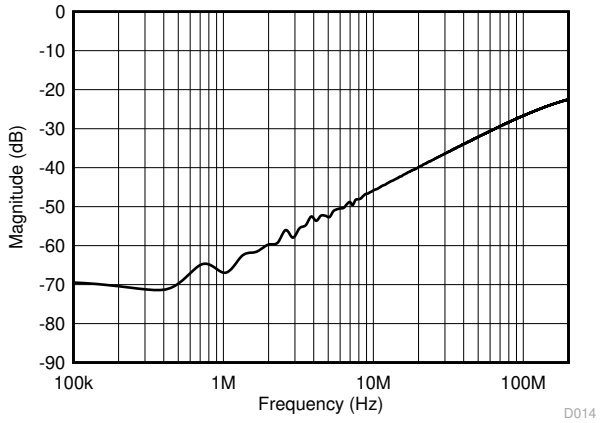
T_A = -40°C to 125°C

図 5-12. Charge Injection vs Drain Voltage



T_A = 25°C

図 5-13. Output $T_{TRANSITION}$ vs Supply Voltage

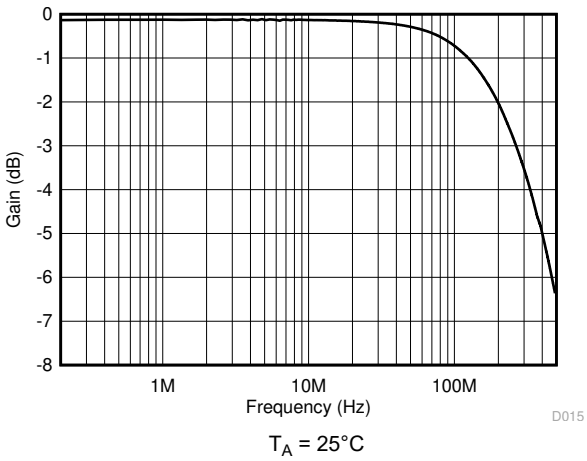


T_A = 25°C

図 5-14. Xtalk and Off-Isolation vs Frequency

Typical Characteristics

at T_A = 25°C, V_{DD} = 5V (unless otherwise noted)



T_A = 25°C

図 5-15. On Response vs Frequency

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6 Parameter Measurement Information

6.1 On-Resistance

The on-resistance of a device is the ohmic resistance between the source (Sx) and drain (D) pins of the device. The on-resistance varies with input voltage and supply voltage. The symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in 図 6-1. Voltage (V) and current (I_{SD}) are measured using this setup, and R_{ON} is computed with $R_{ON} = V / I_{SD}$:

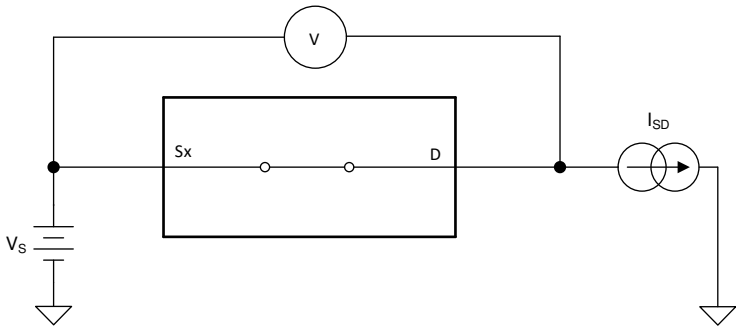


図 6-1. On-Resistance Measurement Setup

6.2 Off-Leakage Current

Source leakage current is defined as the leakage current flowing into or out of the source pin when the switch is off. This current is denoted by the symbol $I_{S(OFF)}$.

The setup used to measure off-leakage current is shown in 図 6-2.

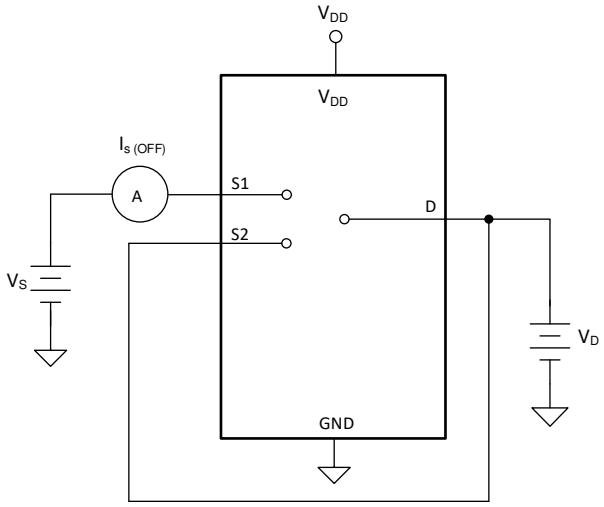


図 6-2. Off-Leakage Measurement Setup

6.3 On-Leakage Current

Source on-leakage current is defined as the leakage current flowing into or out of the source pin when the switch is on. This current is denoted by the symbol $I_{S(ON)}$.

Drain on-leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is on. This current is denoted by the symbol $I_{D(ON)}$.

Either the source pin or drain pin is left floating during the measurement. 図 6-3 shows the circuit used for measuring the on-leakage current, denoted by $I_{S(ON)}$ or $I_{D(ON)}$.

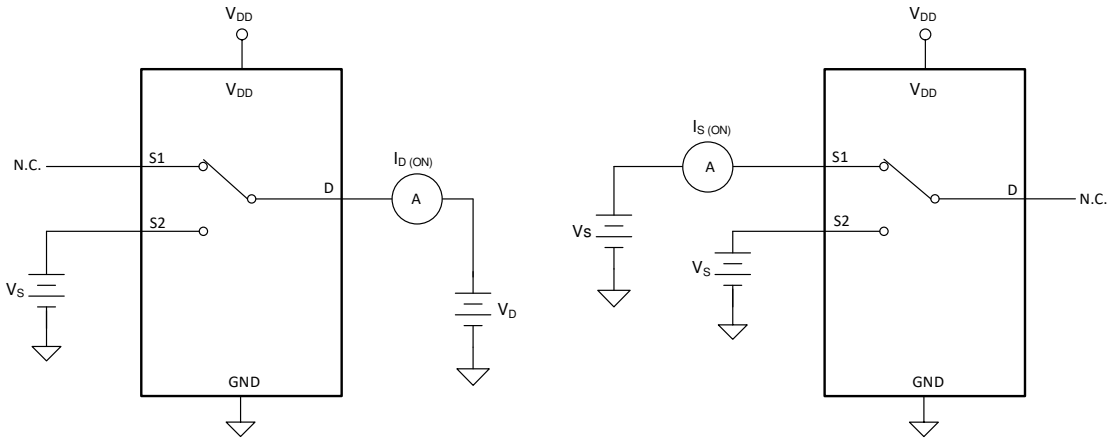


図 6-3. On-Leakage Measurement Setup

6.4 Transition Time

Transition time is defined as the time taken by the output of the device to rise or fall 10% after the address signal has risen or fallen past the logic threshold. The 10% transition measurement is utilized to provide the timing of the device. System level timing can then account for the time constant added from the load resistance and load capacitance. 図 6-4 shows the setup used to measure transition time, denoted by the symbol $t_{TRANSITION}$.

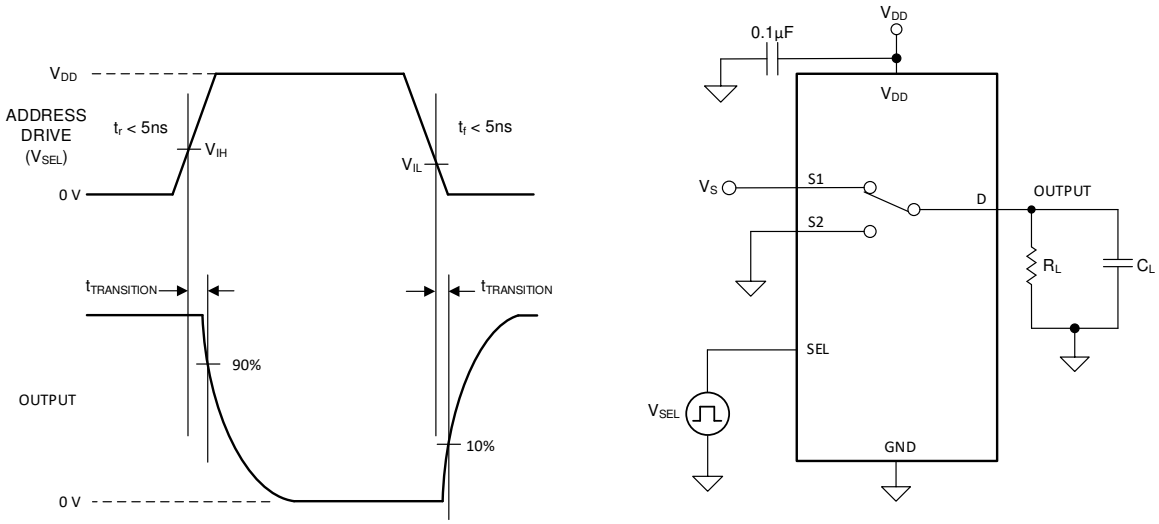


図 6-4. Transition-Time Measurement Setup

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6.5 Break-Before-Make

Break-before-make delay is a safety feature that prevents two inputs from connecting when the device is switching. The output first breaks from the on-state switch before making the connection with the next on-state switch. The time delay between the *break* and the *make* is known as break-before-make delay. 図 6-5 shows the setup used to measure break-before-make delay, denoted by the symbol $t_{OPEN(BBM)}$.

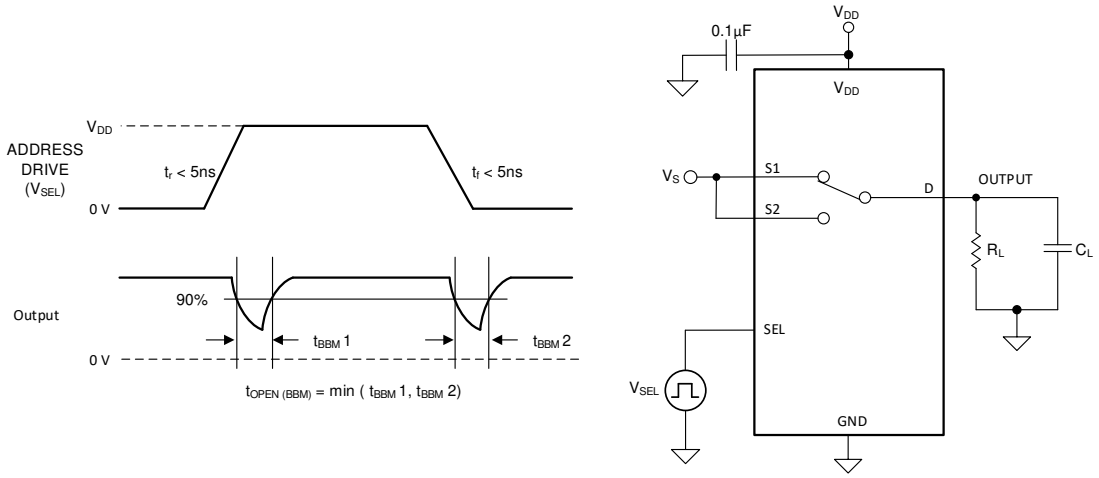


図 6-5. Break-Before-Make Delay Measurement Setup

6.6 Charge Injection

The TMUX1119 has a transmission-gate topology. Any mismatch in capacitance between the NMOS and PMOS transistors results in a charge injected into the drain or source during the falling or rising edge of the gate signal. The amount of charge injected into the source or drain of the device is known as charge injection, and is denoted by the symbol Q_C. 図 6-6 shows the setup used to measure charge injection from Drain (D) to Source (Sx).

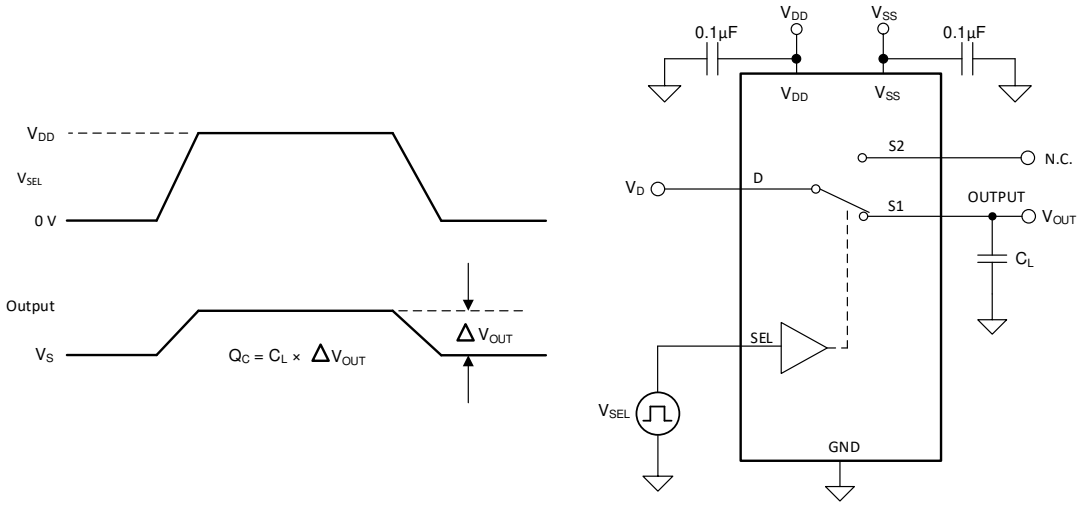


図 6-6. Charge-Injection Measurement Setup

6.7 Off Isolation

Off isolation is defined as the ratio of the signal at the drain pin (D) of the device when a signal is applied to the source pin (Sx) of an off-channel. 図 6-7 shows the setup used to measure, and the equation used to calculate off isolation.

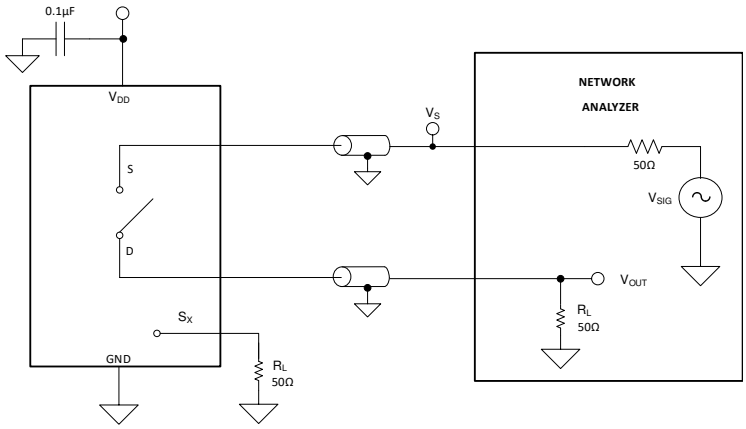


図 6-7. Off Isolation Measurement Setup

$$\text{Off Isolation} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (1)$$

6.8 Crosstalk

Crosstalk is defined as the ratio of the signal at the drain pin (D) of a different channel, when a signal is applied at the source pin (Sx) of an on-channel. 図 6-8 shows the setup used to measure, and the equation used to calculate crosstalk.

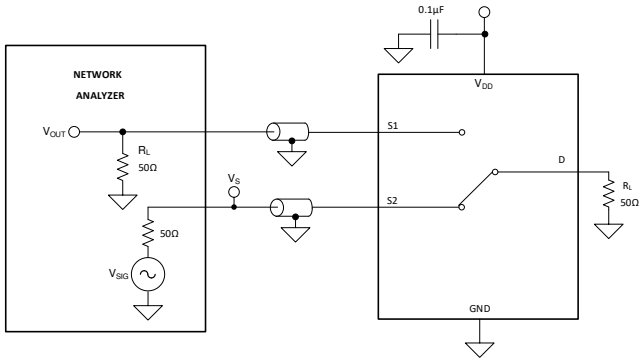


図 6-8. Crosstalk Measurement Setup

$$\text{Channel-to-Channel Crosstalk} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (2)$$

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6.9 Bandwidth

Bandwidth is defined as the range of frequencies that are attenuated by less than 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (D) of the device. 図 6-9 shows the setup used to measure bandwidth.

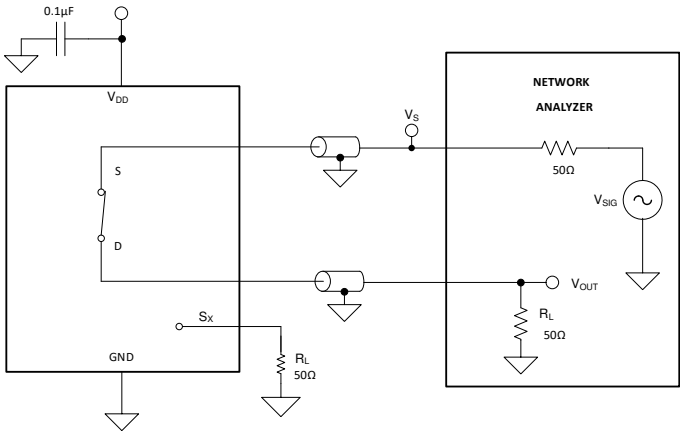


図 6-9. Bandwidth Measurement Setup

7 Detailed Description

7.1 Overview

The TMUX1119 is an 2:1, 1-ch. (SPDT), analog switch where the input is controlled with a single select (SEL) control pin.

7.2 Functional Block Diagram

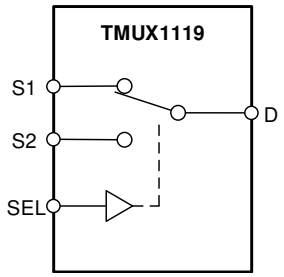


図 7-1. TMUX1119 Functional Block Diagram

7.3 Feature Description

7.3.1 Bidirectional Operation

The TMUX1119 conducts equally well from source (Sx) to drain (D) or from drain (D) to source (Sx). The device has very similar characteristics in both directions and supports both analog and digital signals.

7.3.2 Rail to Rail Operation

The valid signal path input/output voltage for TMUX1119 ranges from GND to V_{DD}.

7.3.3 1.8V Logic Compatible Inputs

The TMUX1119 has 1.8V logic compatible control for the logic control input (SEL). The logic input threshold scales with supply but still provide 1.8V logic control when operating at 5.5V supply voltage. 1.8V logic level inputs allow the TMUX1119 to interface with processors that have lower logic I/O rails and eliminates the need for an external translator, which saves both space and BOM cost. For more information on 1.8V logic implementations refer to *Simplifying Design with 1.8V logic Muxes and Switches*

7.3.4 Fail-Safe Logic

The TMUX1119 supports Fail-Safe Logic on the control input pin (SEL) allowing for operation up to 5.5V, regardless of the state of the supply pin. This feature allows voltages on the control pin to be applied before the supply pin, protecting the device from potential damage. Fail-Safe Logic minimizes system complexity by removing the need for power supply sequencing on the logic control pins. For example, the Fail-Safe Logic feature allows the select pin of the TMUX1119 to be ramped to 5.5V while V_{DD} = 0V. Additionally, the feature enables operation of the TMUX1119 with V_{DD} = 1.2V while allowing the select pin to interface with a logic level of another device up to 5.5V.

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7.3.5 Ultra-Low Leakage Current

The TMUX1119 provides extremely low on-leakage and off-leakage currents. The TMUX1119 is capable of switching signals from high source-impedance inputs into a high input-impedance op amp with minimal offset error because of the ultra-low leakage currents. 図 7-2 shows typical leakage currents of the TMUX1119 versus temperature.

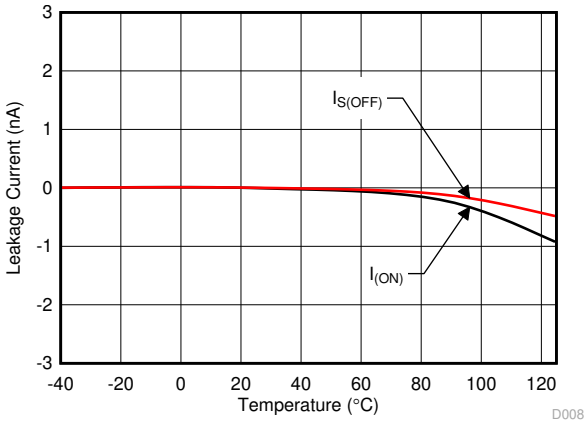


図 7-2. Leakage Current vs Temperature

7.3.6 Ultra-Low Charge Injection

The TMUX1119 has a transmission gate topology, as shown in 図 7-3. Any mismatch in the stray capacitance associated with the NMOS and PMOS causes an output level change whenever the switch is opened or closed.

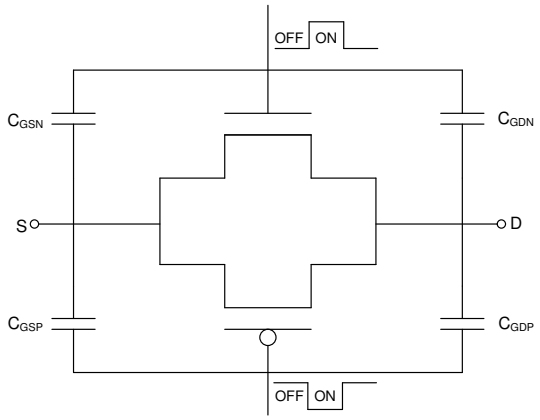


図 7-3. Transmission Gate Topology

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The TMUX1119 has special charge-injection cancellation circuitry that reduces the drain-to-source charge injection to -6pC at V_D = 1V as shown in 図 7-4.

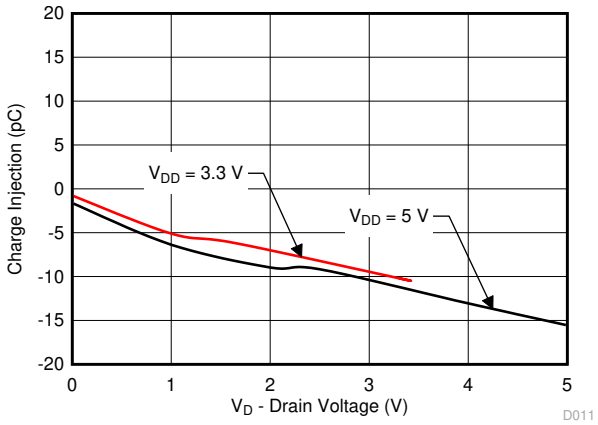


図 7-4. Charge Injection vs Drain Voltage

7.4 Device Functional Modes

The select (SEL) pin of the TMUX1119 controls which switch is connected to the drain of the device. When a given input is not selected, that source pin is in high impedance mode (HI-Z). The control pins can be as high as 5.5V.

7.5 Truth Tables

表 7-1. TMUX1119 Truth Table

CONTROL LOGIC (SEL)	Selected Source (Sx) Connected To Drain (D) Pin
0	S1
1	S2

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8 Application and Implementation

注

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8.1 Application Information

The TMUX11xx family offers ultra-low input and output leakage currents and low charge injection. These devices operate up to 5.5V, and offer true rail-to-rail input and output of both analog and digital signals. The TMUX1119 has a low on-capacitance which allows faster settling time when multiplexing inputs in the time domain. These features make the TMUX11xx devices a family of precision, high-performance switches and multiplexers for low-voltage applications.

8.2 Typical Application

図 8-1 shows an ultrasonic gas meter front end. The ultrasonic front end design utilizes time of flight (TOF) measurement to determine the amount of gas flowing in a pipe. The circuit utilizes the MSP430FR5994, two ultra low power operational amplifiers, OPA835 and OPA836, along with two TMUX1119, 2:1 precision switches.

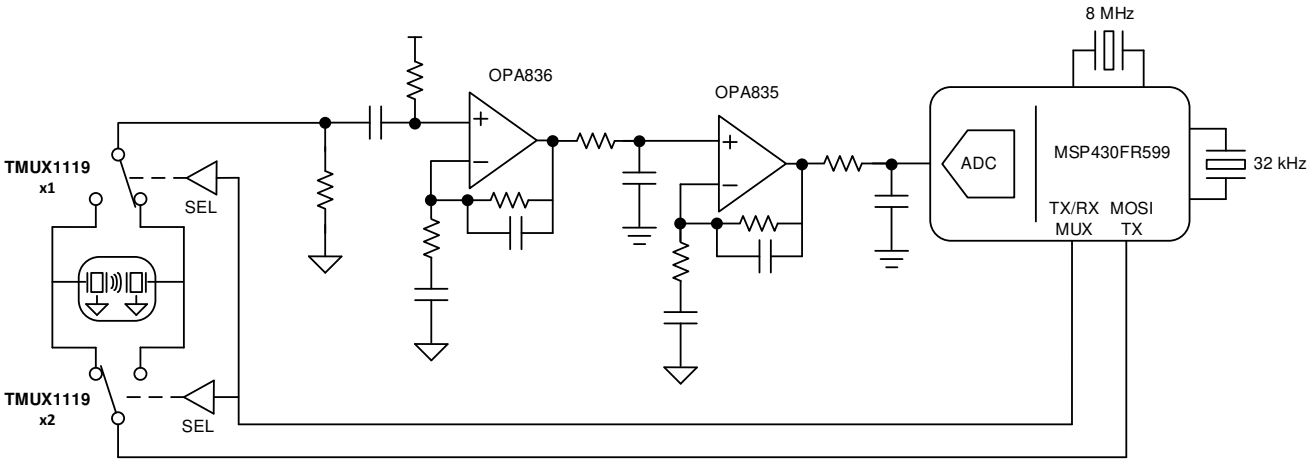


図 8-1. Ultrasonic Gas Meter System

8.2.1 Design Requirements

For this design example, use the parameters listed in 表 8-1.

表 8-1. Design Parameters

PARAMETERS	VALUES
Supply (V_{DD})	5V
I/O signal range	0V to V_{DD} (Rail to Rail)
Control logic thresholds	1.8V compatible
Single-shot standard deviation (STD)	<2ns
Zero-flow drift (ZFD)	<1ns

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8.2.2 Detailed Design Procedure

The TMUX1119 can be operated without any external components except for the supply decoupling capacitors. All inputs passing through the switch must fall within the recommend operating conditions of the TMUX1119, including signal range and continuous current. For this design with a supply of 5V the signal range can be 0V to 5V, and the maximum continuous current can be 30mA.

The TMUX1119 device is a bidirectional, single-pole double-throw (SPDT) switch that offers low on-resistance, low leakage, and low power. These features make this device suitable for portable and power sensitive applications such as ultrasonic gas metering systems. The two TMUX1119 devices are used to switch the transmission and reception signals from the MCU to the two transceivers in an efficient manner without distortion. Exceptional on-resistance flatness, leakage performance, and charge injection allows the TMUX1119 to be utilized in place of the TS5A9411 in *Ultrasonic Gas Meter Front-End With MSP430™ Reference Design*. For a more detailed analysis of the entire system refer to the *reference design*.

8.2.3 Application Curve

The TMUX1119 is capable of switching signals with minimal distortion because of the ultra-low leakage currents and excellent On-resistance flatness. 図 8-2 shows how the on-resistance of the TMUX1119 varies with different supply voltages.

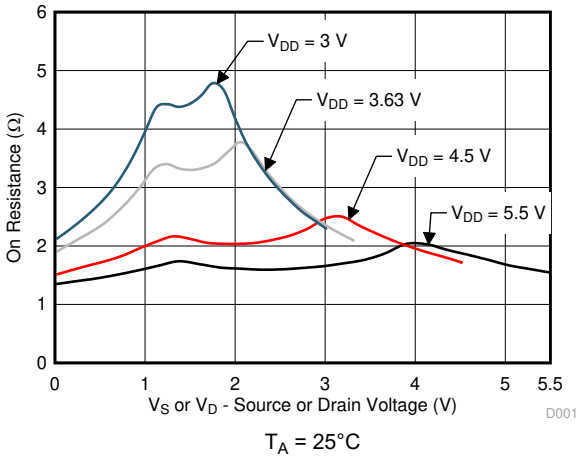


図 8-2. On-Leakage vs Source or Drain Voltage

8.3 Power Supply Recommendations

The TMUX1119 operates across a wide supply range of 1.08V to 5.5V. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings can cause permanent damage to the devices.

Power-supply bypassing improves noise margin and prevents switching noise propagation from the V_{DD} supply to other components. Good power-supply decoupling is important to achieve optimum performance. For improved supply noise immunity, use a supply decoupling capacitor ranging from 0.1µF to 10µF from V_{DD} to ground. Place the bypass capacitors as close to the power supply pins of the device as possible using low-impedance connections. TI recommends using multi-layer ceramic chip capacitors (MLCCs) that offer low equivalent series resistance (ESR) and inductance (ESL) characteristics for power-supply decoupling purposes. For very sensitive systems, or for systems in harsh noise environments, avoiding the use of vias for connecting the capacitors to the device pins may offer superior noise immunity. The use of multiple vias in parallel lowers the overall inductance and is beneficial for connections to ground planes.

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8.4 Layout

8.4.1 Layout Guidelines

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 図 8-3 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

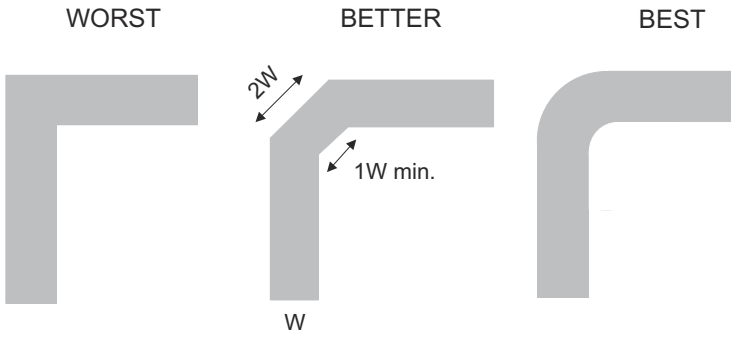


図 8-3. Trace Example

Route high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points, through-hole pins are not recommended at high frequencies.

図 8-4 shows an example of a PCB layout with the TMUX1119. Some key considerations are as follows:

- Decouple the V_{DD} pin with a 0.1µF capacitor, placed as close to the pin as possible. Ensure that the capacitor voltage rating is sufficient for the V_{DD} supply.
- Keep the input lines as short as possible.
- Use a solid ground plane to help reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

8.4.2 Layout Example

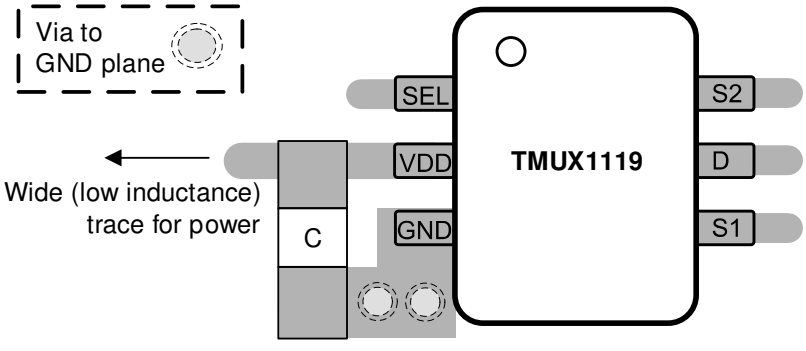


図 8-4. TMUX1119 Layout Example

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Ultrasonic Gas Meter Front-End With MSP430™ Reference Design*.
- Texas Instruments, *True Differential, 4 x 2 MUX, Analog Front End, Simultaneous-Sampling ADC Circuit*.
- Texas Instruments, *Improve Stability Issues with Low CON Multiplexers*.
- Texas Instruments, *Simplifying Design with 1.8V logic Muxes and Switches*.
- Texas Instruments, *Eliminate Power Sequencing with Powered-off Protection Signal Switches*.
- Texas Instruments, *System-Level Protection for High-Voltage Analog Multiplexers*.
- Texas Instruments, *QFN/SON PCB Attachment*.
- Texas Instruments, *Quad Flatpack No-Lead Logic Packages*.

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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9.6 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision B (May 2020) to Revision C (February 2024)	Page
• Updated Is or Id (Continuous Current) values	3
• Added Ipeak values to *Recommended Operating Conditions* table	3

Changes from Revision A (November 2019) to Revision B (May 2020)	Page
• DBV パッケージのステータスを次のように変更：「製品プレビュー」から*量産データに更新*	1

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- Added Thermal information for DBV package....4

Changes from Revision * (December 2018) to Revision A (November 2019) **Page**

- データシートのタイトルを次のように変更:「高精度アナログ マルチプレクサ」から *高精度スイッチ* 1
- *「アプリケーション」*の一覧を変更....1
- Changed Thermal Information for DCK package.... 4

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX1119DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	26HT	Samples
TMUX1119DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1DF	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

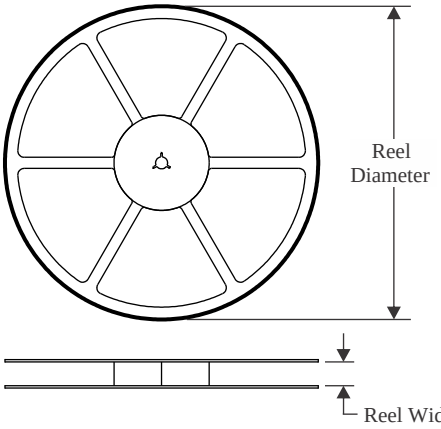
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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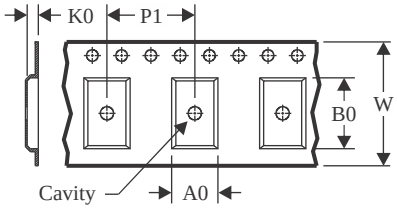
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TAPE AND REEL INFORMATION

REEL DIMENSIONS

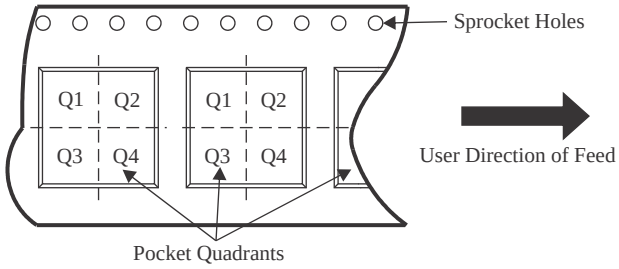


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

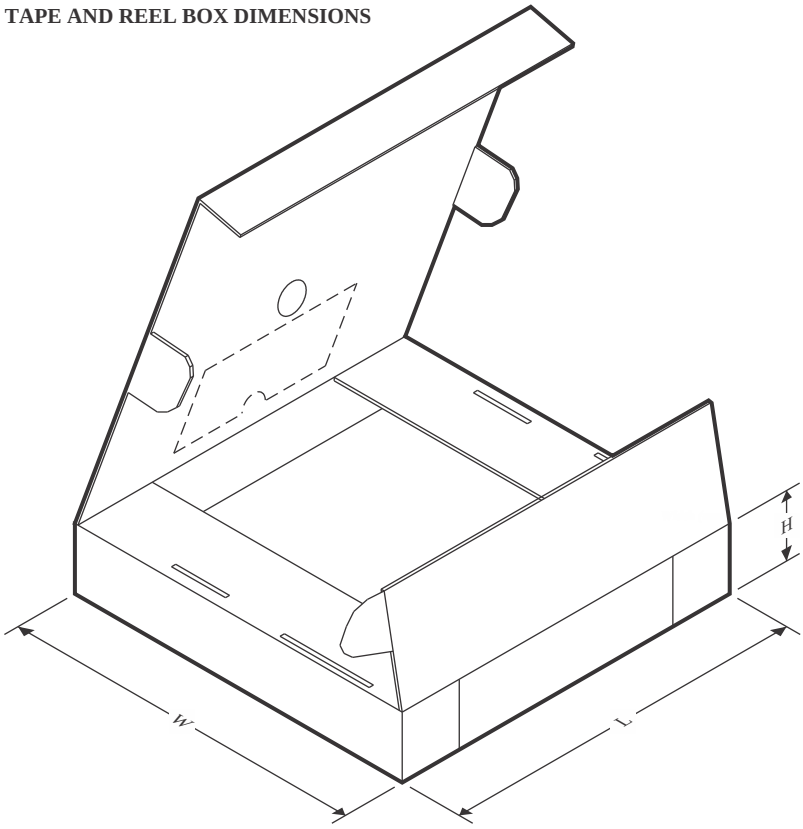
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX1119DBVR	SOT-23	DBV	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TMUX1119DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

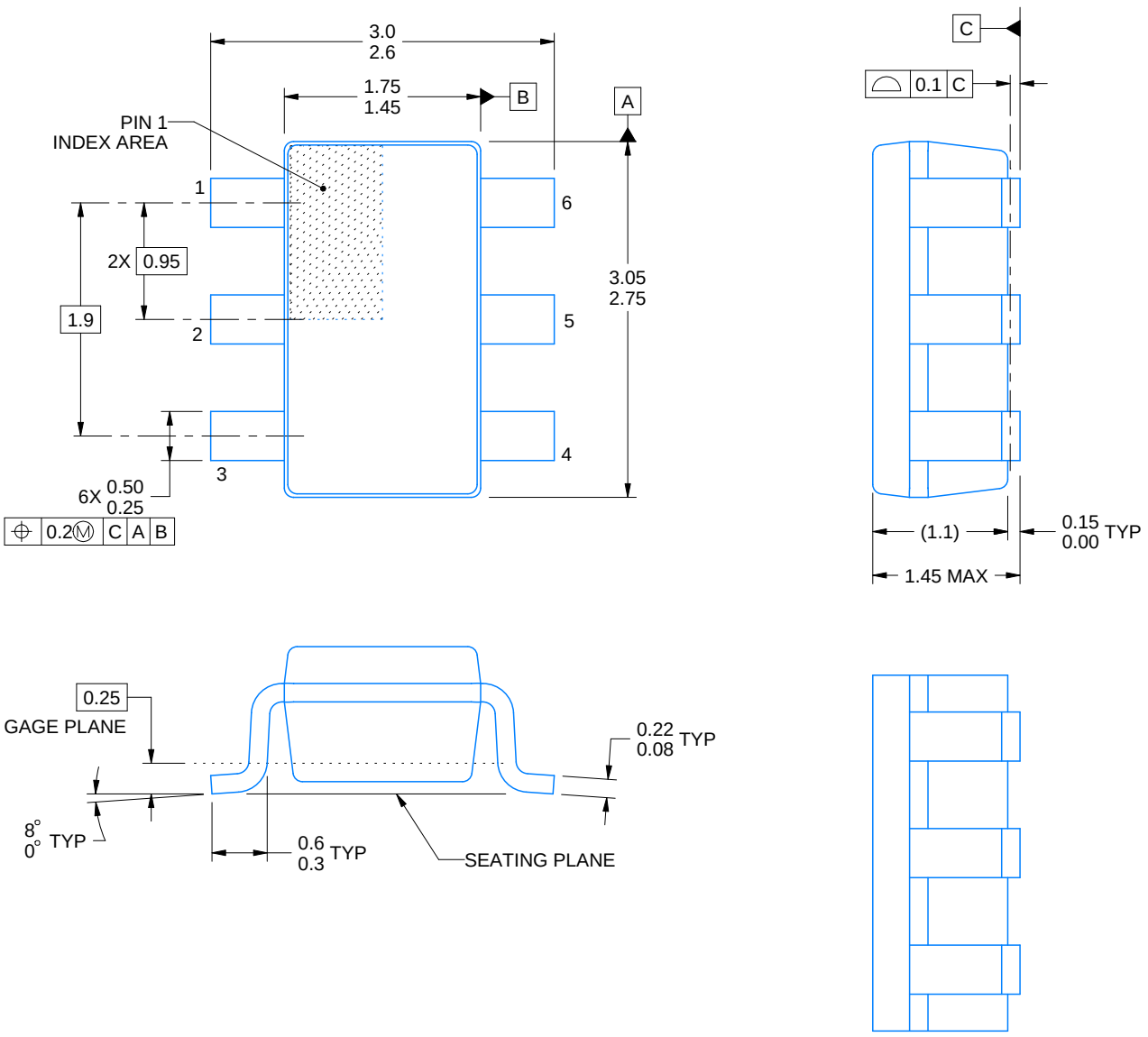
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX1119DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
TMUX1119DCKR	SC70	DCK	6	3000	180.0	180.0	18.0

PACKAGE OUTLINE

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

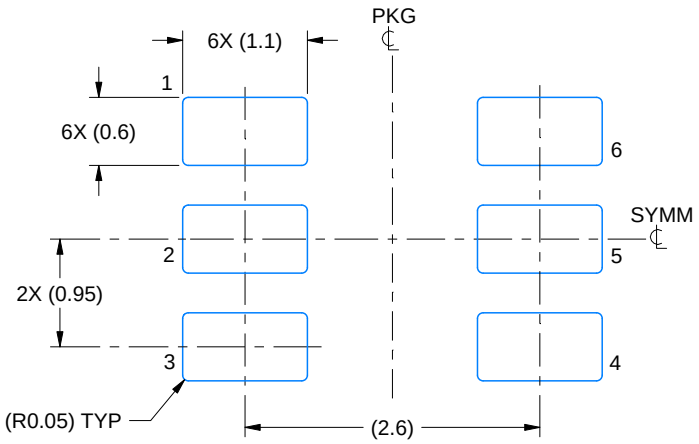


ALTERNATIVE PACKAGE SINGULATION VIEW

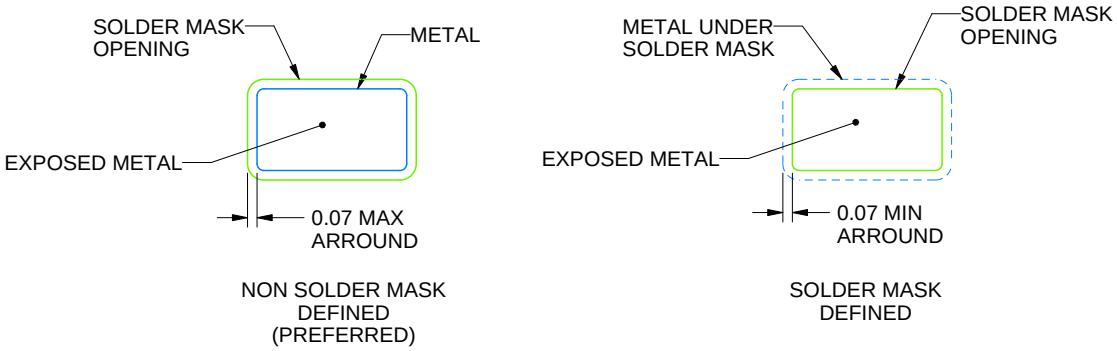
4214840/E 02/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Refernce JEDEC MO-178.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

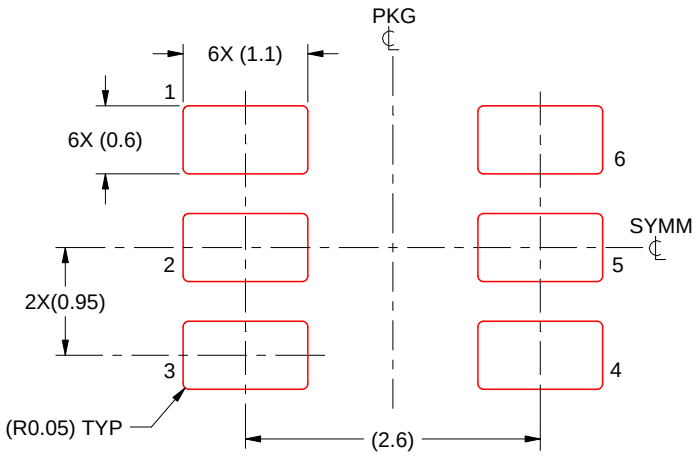


SOLDER MASK DETAILS

4214840/E 02/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



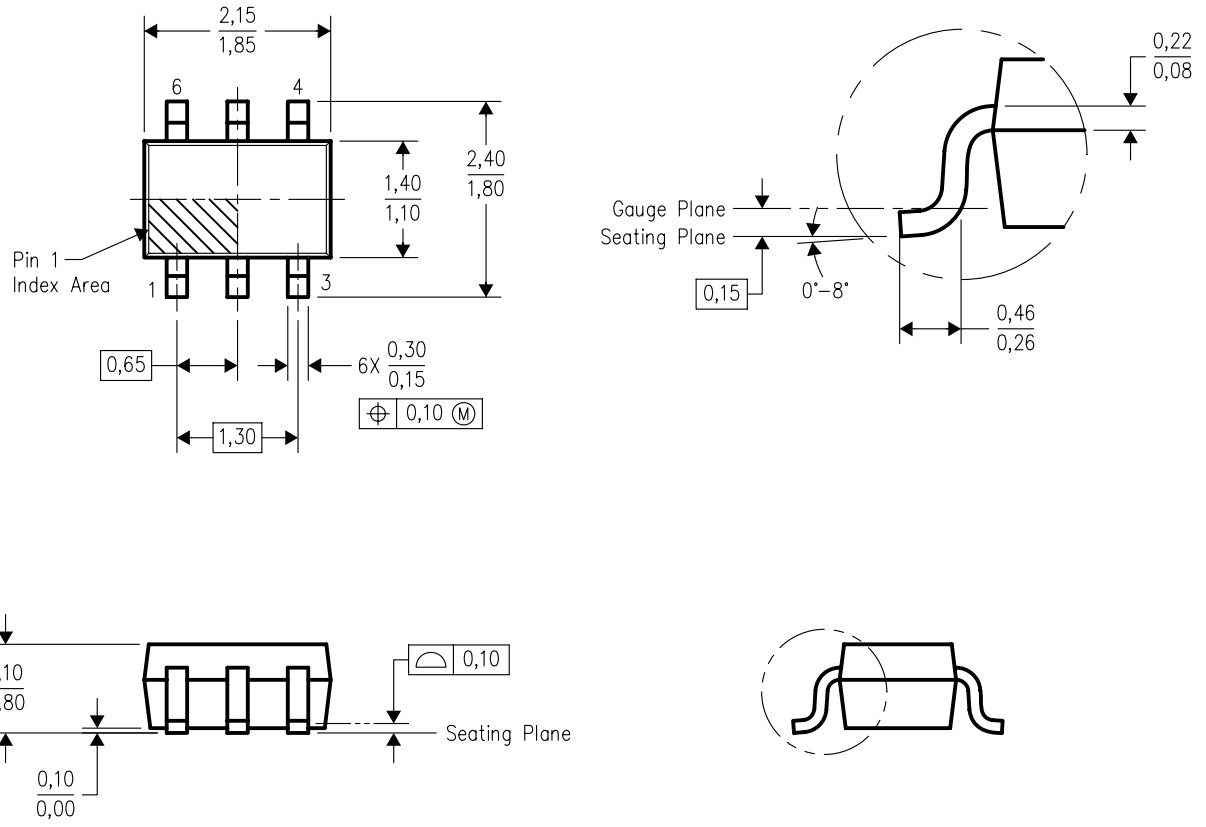
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214840/E 02/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

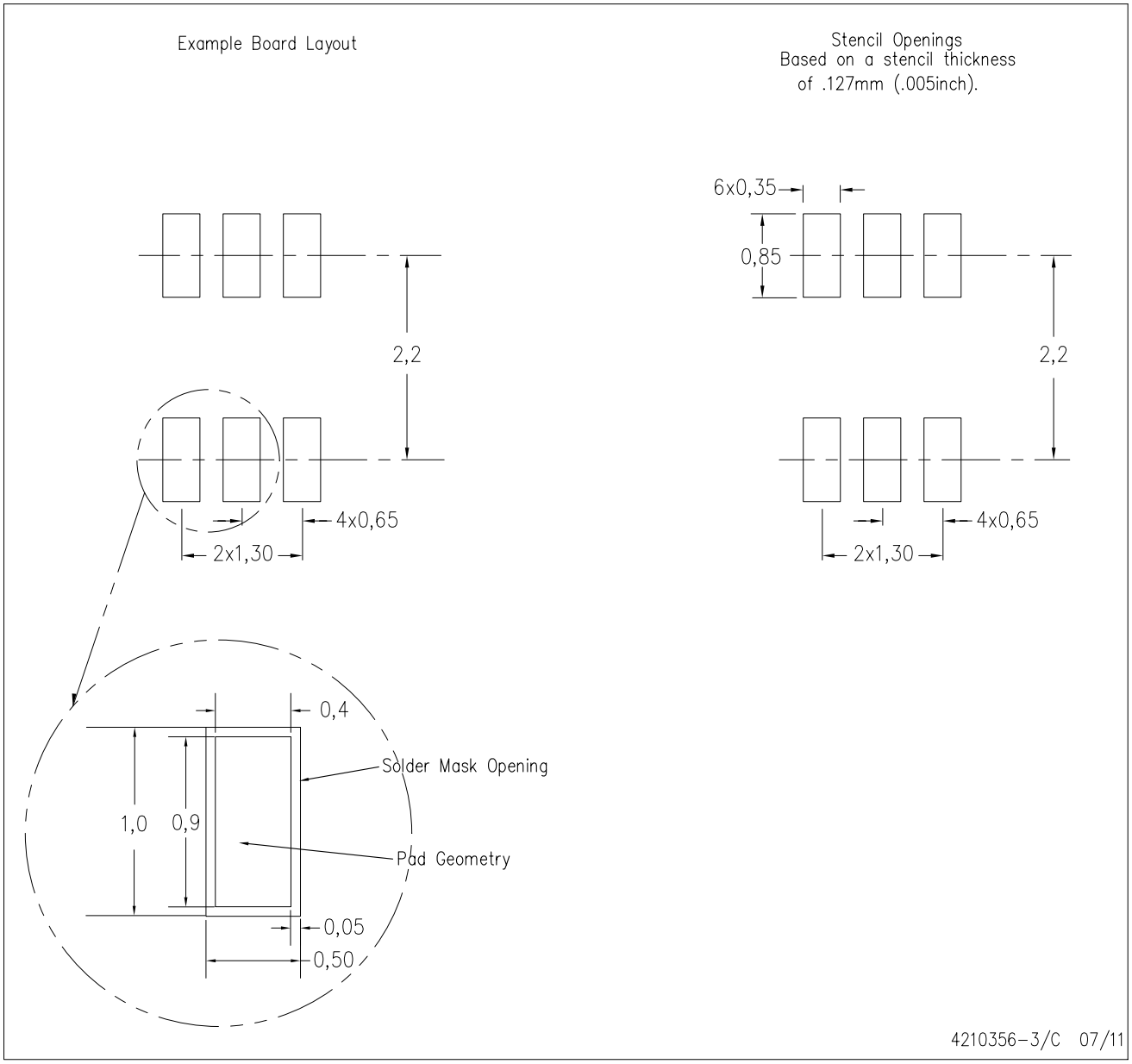
DCK (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



4093553–4/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AB.

DCK (R–PDSO–G6) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

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郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
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